AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (Currently Amended) A semiconductor device comprising:

a dielectric layer;

a silicon-nitride layer superjacent to the dielectric layer, wherein the silicon-nitride layer has been deposited superjacent to the dielectric layer using physical vapor deposition (PVD);

a polysilicon gate layer superjacent to the silicon-nitride layer.

2. (Canceled)

3. (Currently Amended) The semiconductor device of claim 1 ~~claim 2~~ wherein the dielectric layer has a dielectric constant of twenty or greater.

4. (Original) The semiconductor device of claim 3 wherein the polysilicon gate layer is n-type.

5. (Original) The semiconductor device of claim 3 wherein the polysilicon gate layer is p-type.

6. (Original) The semiconductor device of claim 1 wherein the semiconductor device is a complimentary metal-oxide-semiconductor device.

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7-12. (Canceled)

13. (Currently Amended) An apparatus comprising:

a gate structure including a silicon-nitride layer formed using a physical vapor deposition (PVD) process;

a substrate coupled to the gate structure;

a drain coupled to the substrate;

a source coupled to the substrate.

14. (Canceled)

15. (Original) The apparatus of claim 13 wherein the gate structure further includes a dielectric layer coupled to the silicon-nitride layer, the dielectric layer having a dielectric constant greater than twenty.

16. (Original) The apparatus of claim 13 wherein the gate structure further includes a polysilicon layer coupled to the silicon-nitride layer.

17. (Original) The apparatus of claim 16 wherein the polysilicon layer comprises n-type material.

18. (Original) The apparatus of claim 16 wherein the polysilicon layer comprises p-type material.

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19. (Original) The apparatus of claim 13 wherein the gate structure is part of a complimentary metal-oxide-semiconductor device.

20-25. (Canceled)

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